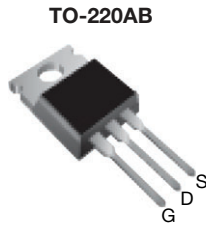


## Power MOSFET



N-Channel MOSFET

### FEATURES

- Low gate charge  $Q_g$  results in simple drive requirement
- Improved gate, avalanche and dynamic  $dV/dt$  ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective  $C_{oss}$  specified
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


 Available  
**RoHS\***  
 Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

### TYPICAL SMPS TOPOLOGIES

- Single transistor flyback Xfmr. reset
- Single transistor forward Xfmr. reset (both US line input only)

PRODUCT SUMMARY	
$V_{DS}$ (V)	400
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$ 1.0
$Q_g$ max. (nC)	22
$Q_{gs}$ (nC)	5.8
$Q_{gd}$ (nC)	9.3
Configuration	Single

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF730APbF
Lead (Pb)-free and halogen-free	IRF730APbF-BE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	400	V	
Gate-source voltage		$V_{GS}$	$\pm 30$		
Continuous drain current	$V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	5.5	A
			$T_C = 100\text{ }^\circ\text{C}$	3.5	
Pulsed drain current <sup>a</sup>		$I_{DM}$	22		
Linear derating factor			0.6	W/ $^\circ\text{C}$	
Single pulse avalanche energy <sup>b</sup>		$E_{AS}$	290	mJ	
Repetitive avalanche current <sup>a</sup>		$I_{AR}$	5.5	A	
Repetitive avalanche energy <sup>a</sup>		$E_{AR}$	7.4	mJ	
Maximum power dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	74	W	
Peak diode recovery $dV/dt$ <sup>c</sup>		$dV/dt$	4.6	V/ns	
Operating junction and storage temperature range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$	
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s		300		
Mounting torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 19\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 5.5\text{ A}$  (see fig. 12)
- $I_{SD} \leq 5.5\text{ A}$ ,  $dI/dt \leq 90\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case



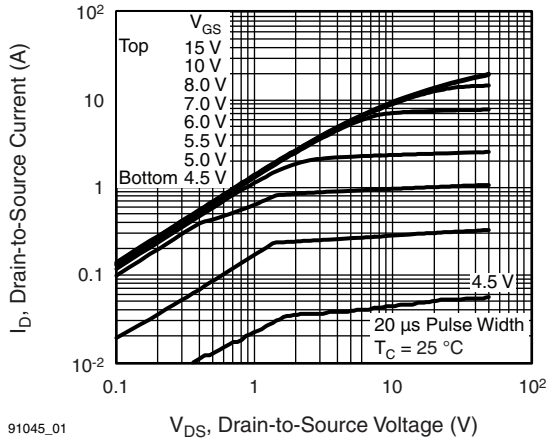
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJC}$	-	1.70	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJA}$	-	62	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	400	-	-	V	
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	0.5	-	V/°C	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.5	V	
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	$\mu\text{A}$	
		$V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.3\text{ A}^b$	-	-	1.0	$\Omega$	
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 3.3\text{ A}$	3.1	-	-	S	
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5	-	600	-	pF	
Output capacitance	$C_{oss}$		-	103	-		
Reverse transfer capacitance	$C_{rss}$		-	4.0	-		
Output capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	890	-	
Effective output capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 320\text{ V}, f = 1.0\text{ MHz}$	-	30	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 0\text{ V to } 320\text{ V}^c$	-	45	-	
Gate-source charge	$Q_{gs}$		$I_D = 3.5\text{ A}, V_{DS} = 320\text{ V}$ see fig. 6 and 13 <sup>b</sup>	-	-	22	nC
Gate-drain charge	$Q_{gd}$			-	-	9.3	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 200\text{ V}, I_D = 3.5\text{ A}$ $R_g = 12\text{ }\Omega, R_D = 57\text{ }\Omega$ , see fig. 10 <sup>b</sup>	-	10	-	ns	
Rise time	$t_r$		-	22	-		
Turn-off delay time	$t_{d(off)}$		-	20	-		
Fall time	$t_f$		-	16	-		
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	2.7	-	10.9	$\Omega$	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.5	A	
Pulsed diode forward current <sup>a</sup>	$I_{SM}$		-	-	22		
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 5.5\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.6	V	
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	370	550	ns	
Body diode reverse recovery charge	$Q_{rr}$		-	1.6	2.4	$\mu\text{C}$	
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

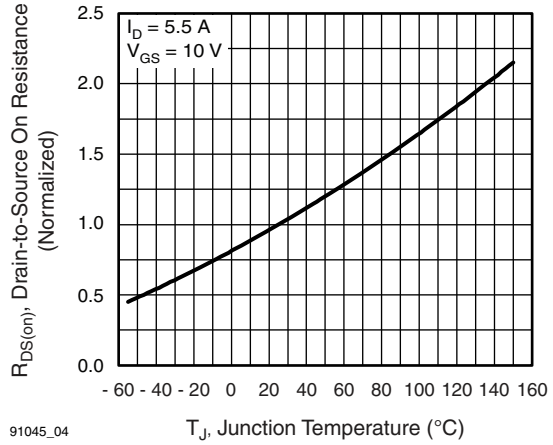
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$
- c.  $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



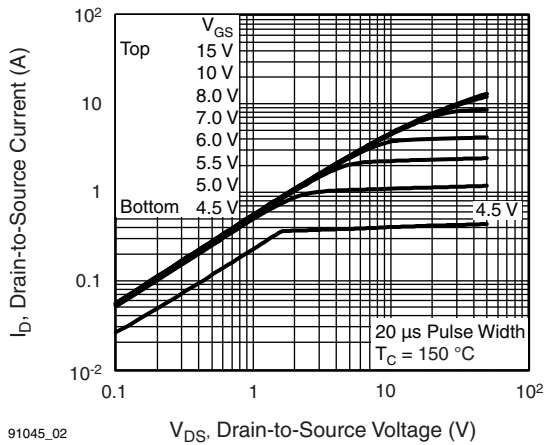
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**Fig. 1 - Typical Output Characteristics**



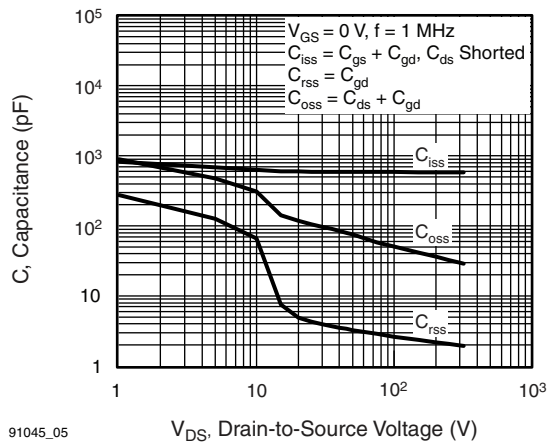
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**Fig. 4 - Normalized On-Resistance vs. Temperature**



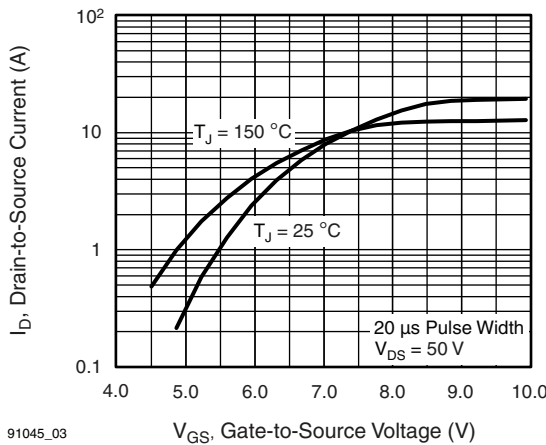
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**Fig. 2 - Typical Output Characteristics**



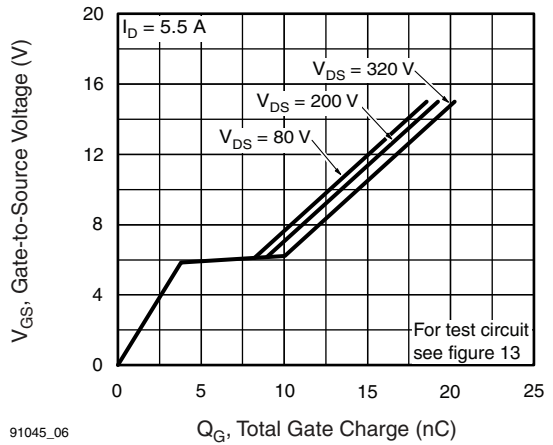
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**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



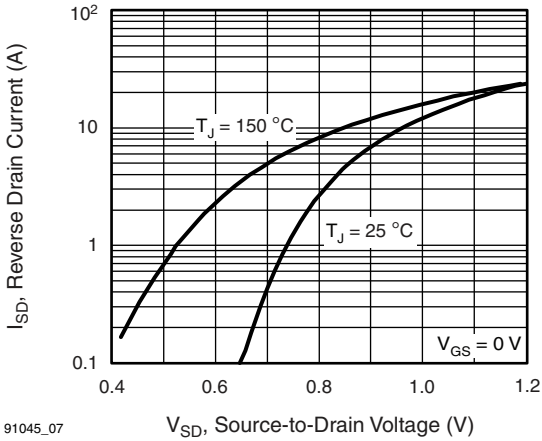
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**Fig. 3 - Typical Transfer Characteristics**



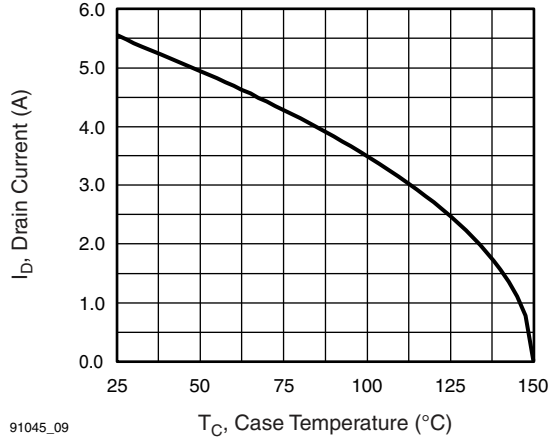
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**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



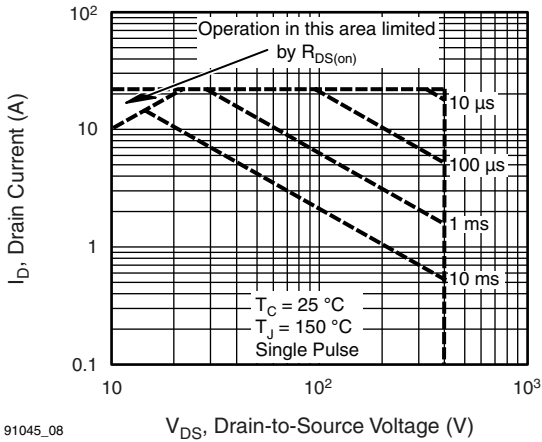
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 9 - Maximum Drain Current vs. Case Temperature



91045\_08

Fig. 8 - Maximum Safe Operating Area

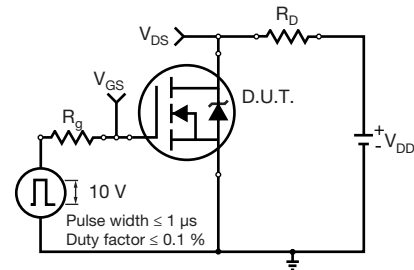


Fig. 10 - Switching Time Test Circuit

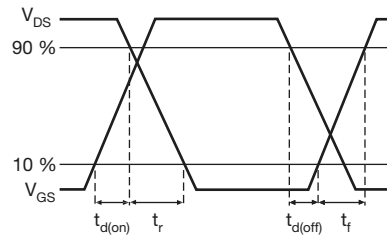
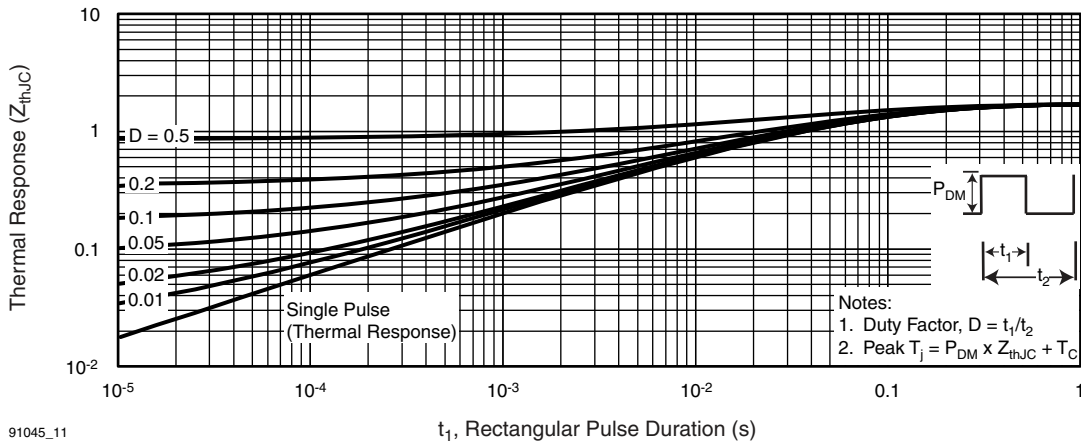


Fig. 11 - Switching Time Waveforms



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Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

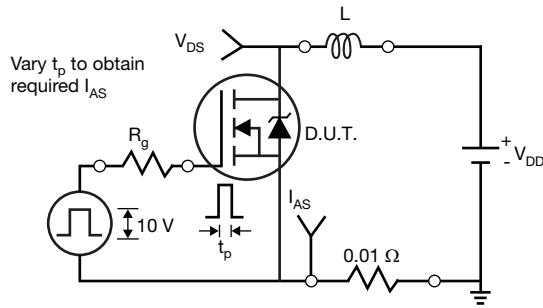


Fig. 13 - Unclamped Inductive Test Circuit

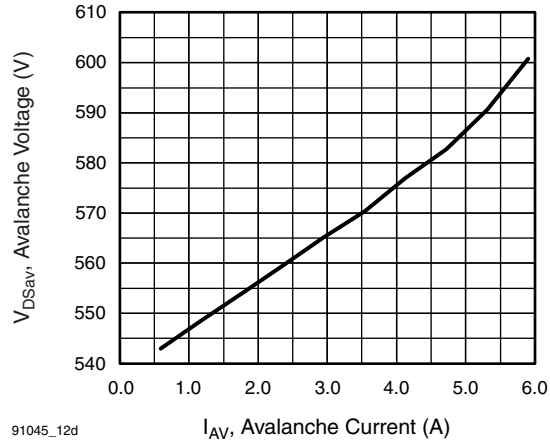


Fig. 16 - Typical Drain Source Voltage vs. Avalanche Current

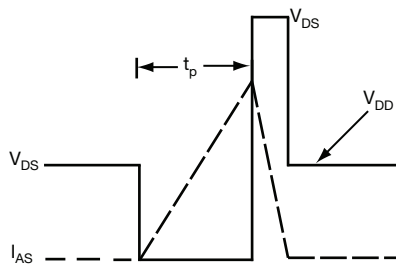


Fig. 14 - Unclamped Inductive Waveforms

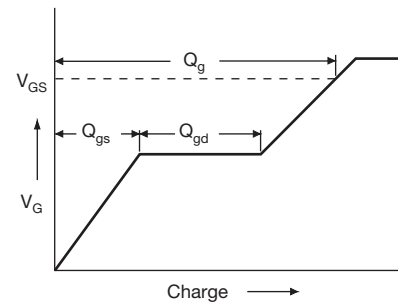


Fig. 17 - Basic Gate Charge Waveform

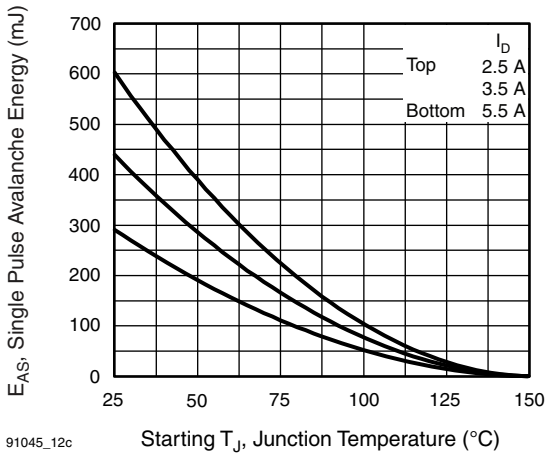


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

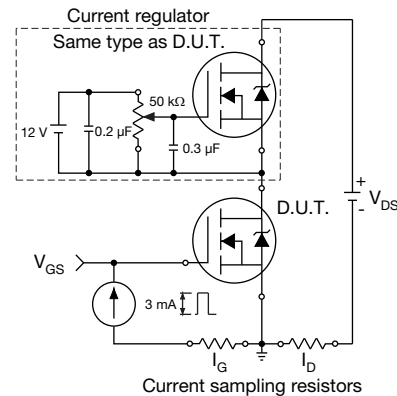
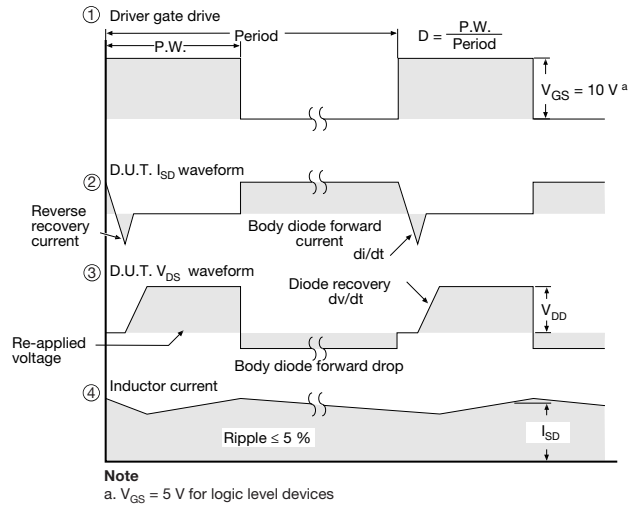
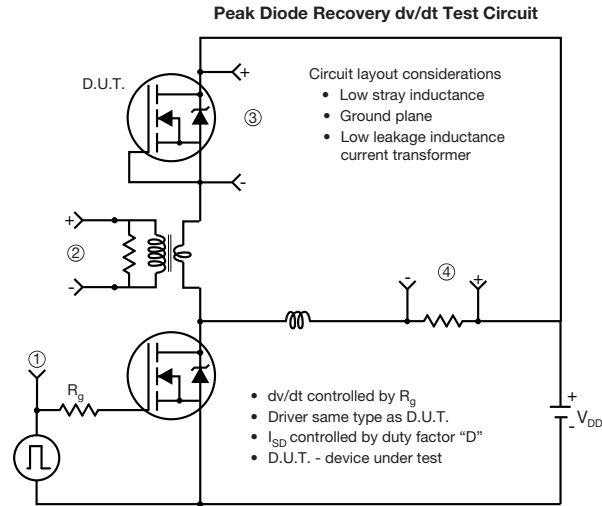


Fig. 18 - Gate Charge Test Circuit



**Fig. 19 - For N-Channel**

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### TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021  
DWG: 6031

#### Note

- $M^*$  = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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